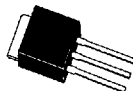


2SJ192



2083A



2092A

LD (Low Drive) Series $V_{DS} = 60V$

P Channel Power MOSFET

©3765

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

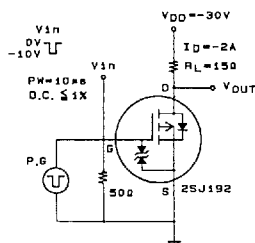
Absolute Maximum Ratings at $T_a = 25^\circ C$

			unit
Drain to Source Voltage	V_{DS}	-60	V
Gate to Source Voltage	V_{GS}	±15	V
Drain Current(DC)	I_D	-4	A
Drain Current(Pulse)	I_{DP}	-16	A
Allowable Power Dissipation	P_D	30	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

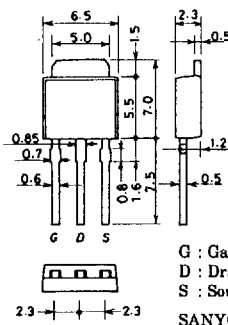
Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DS}$	$I_D = -1mA, V_{GS} = 0$	-60			V
G-S Breakdown Voltage	$V_{(BR)GS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	±15			V
Zero Gate Voltage	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0$			-100	μA
Drain Current						
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -2A$	2.5	4		S
Static Drain to Source	$R_{DS(on)}$	$I_D = -2A, V_{GS} = -10V$		0.15	0.2	Ω
on State Resistance	$R_{dS(on)}$	$I_D = -2A, V_{GS} = -4V$		0.2	0.27	Ω
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		950		pF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		300		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		75		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		15		ns
Rise Time	t_r	"		35		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		115		ns
Fall Time	t_f	"		95		ns
Diode Forward Voltage	V_{SD}	$I_S = -4A, V_{GS} = 0$	-1.0	-1.5		V

Switching Time Test Circuit



Package Dimensions 2083A (unit : mm)



Package Dimensions 2092A (unit : mm)

